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**VERSION WITH MARKINGS TO SHOW CHANGES MADE**

**In the specification:**

Paragraphs beginning at line 19 of page 7 through line 24 of page 8 have been amended as follows:

Figure 1 is a top schematic view of a radial cluster tool for batch processing of semiconductor substrates;

Figure 2A is a top schematic view of one embodiment of an apparatus containing a capping module and high pressure deposition module of the present invention;

Figure 2B is a top schematic view of another embodiment of an apparatus containing a capping module and high pressure deposition module of the present invention;

Figure 3A is a top schematic planar view of one embodiment of a capping module and high pressure deposition module of the present invention;

Figure 3B is a top schematic view of one embodiment of a capping module and high pressure deposition module of the present invention;

Figure 4 is a perspective view of an embodiment of a loadlock chamber of the present invention;

Figure 5 is a top schematic view of a transfer chamber and a processing chamber showing a substrate handling member of the present invention mounted in the transfer chamber and in a retracted position ready for rotation within the transfer chamber or extension into another chamber;

Figure 6 is a top schematic view of a transfer chamber and a processing chamber showing a substrate handling member of the present invention mounted in the transfer chamber and in an extended position wherein the blades are positioned in the processing chamber;

Figure 7 is a cross sectional view of a rapid thermal anneal chamber;

Figure 8 is a perspective view of one embodiment of a PECVD chamber included in the capping module of the present invention;

Figure 9 is a cross sectional view of the PECVD chamber of the present invention;

Figure 10 is an exploded view of the gas distribution assembly for the PECVD chamber;

Figure 11 is a top view of a PECVD chamber of the present invention with the lid removed;

Figure 12 is an illustrative block diagram of the hierarchical control structure of a computer program for process control;

Figure 13 is an illustrative view of the mesoporous film process showing cubic phase structure and mesoporous film structure;

Figure 14 is a cross sectional view showing a dual damascene structure comprising a low k silicon oxide layer and capping layer of the present invention; and

Figures 15A-H are cross sectional views showing a dual damascene deposition sequence of the present inventions.